NSN 5961-01-026-0483

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-026-0483 **Inclosure Material:** Metal **Overall Length:** 1.218 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-59 **Component Name And Quantity:** 2 transistor **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 80.0 breakdown voltage, collector-to-base, emitter open all transistor **Current Rating Per Characteristic:** 10.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 30.0 milliwatts small-signal input power, common-collector all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: npn **Thread Series Designator: Terminal Type And Quantity:** 3 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig:

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